

AMENDMENTS TO THE SPECIFICATION

Please replace paragraph [Para 31] with the following amended paragraph:

[0031] FIG. 9 illustrates a side cross-sectional view of a semiconductor substrate with a multi-gate according to an embodiment of the invention. Resist image 460 has been removed using conventional methods. A hard mask (not shown) may also be removed if used. Gate electrode 480 has been provided on fin and portion of a gate stack 470. In the embodiment of FIG. 9, gate electrode 480 is shown to cover the fin and portion of a gate stack 470 on for the top channel of the tri-gate. However, it is understood that the gate electrode 480 may cover the fin and portion of a gate stack on more or on fewer sides, as desired. Further, one channel may have a different gate configuration than the other channels. By way of example, one channel 445, such as the top channel, may have a first thickness that is greater than the thickness of the remaining channels 475. By way of another example, one channel 445, such as the top channel, may have a different gate dielectric than the remaining channels 475. The top channel 445 may be made of a high-k dielectric, and the gate dielectric of the remaining channels 445 475 may be different material, such as silicon dioxide, nitride oxide, a silicon oxide that has undergone a plasma nitridation process, or other similar materials.